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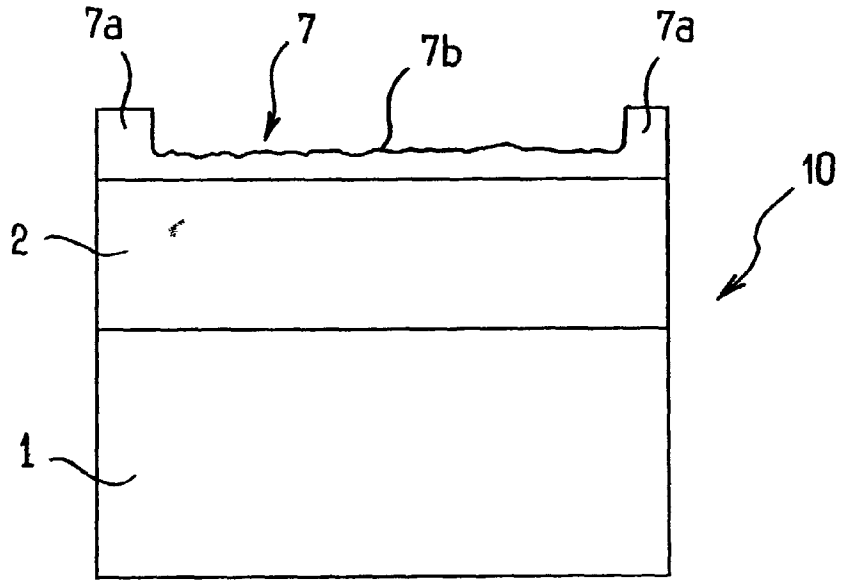
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(54) Title: RECYCLING A WAFER COMPRISING A BUFFER LAYER, AFTER HAVING TAKEN OFF A THIN LAYER THEREFROM



(57) Abstract: Method of recycling a donor wafer (10) after taking off at least one useful layer, the donor wafer (10) comprising successively a substrate (1), a buffer structure (1) and, before taking-off, a useful layer. The method comprises removal of substance relating to part of the donor wafer (10) on the side where the taking-off took place, such that, after removal of substance, there remains at least part of the buffer structure (1) capable of being reused as at least part of a buffer structure (1) during a subsequent taking-off of a useful layer. The present document also relates to: - a method of producing a donor wafer (10) which can be recycled according to the invention; - methods of taking a thin layer off a donor wafer (10) which can be recycled according to the invention; - donor wafers (10) which can be recycled according to the invention.

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